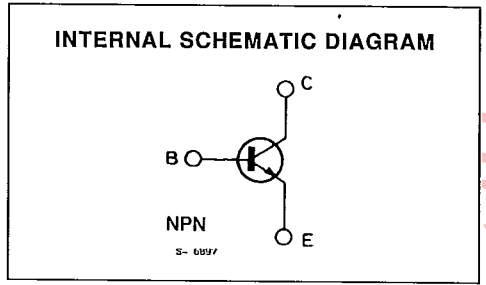
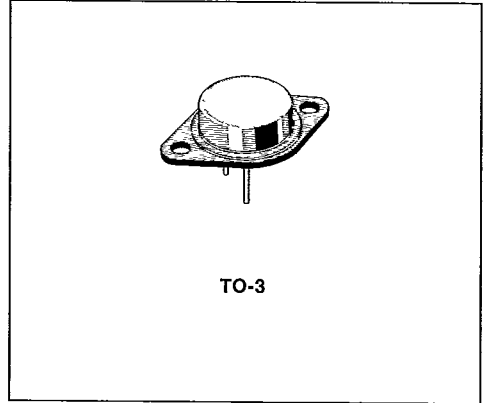


- HIGH EFFICIENCY SWITCHING
- VERY LOW SATURATION VOLTAGE AT 40A
- FAST TURN-OFF AND TURN-ON



**DESCRIPTION**

High current, high speed transistors suited for low voltage applications : high efficiency converters, motor controls.

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value		Unit
		BUV18	BUV19	
V <sub>CBO</sub>	Collector-base Voltage (I <sub>E</sub> = 0)	120	160	V
V <sub>CEO</sub>	Collector-emitter Voltage (I <sub>B</sub> = 0)	60	80	V
V <sub>EB0</sub>	Emitter-base Voltage (I <sub>C</sub> = 0)	7	7	V
I <sub>C</sub>	Collector Current	50	50	A
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5ms)	90	70	A
I <sub>B</sub>	Base Current	16	12	A
I <sub>BM</sub>	Base Peak Current (t <sub>p</sub> < 5ms)	40	30	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> < 25°C	250		W
T <sub>stg</sub>	Storage Temperature	- 65 to 200		°C
T <sub>j</sub>	Max. Operating Junction Temperature	200		°C

**THERMAL DATA**

**S G S-THOMSON**

**30E D**

$R_{thj-case}$	Thermal Resistance Junction-case	max	0.7	°C/W
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**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise specified)

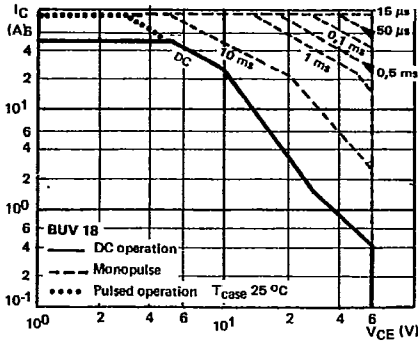
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = V_{CEX}$ $V_{BE} = -1.5V$ $V_{CE} = V_{CEX}$ $V_{BE} = -1.5V$ $T_c = 100^{\circ}C$			1 3	mA mA
$I_{EBO}$	Emitter Cutoff Current ( $I_C = 0$ )	$V_{EB} = 5V$			1	mA
$V_{CEO(sus)}^*$	Collector Emitter Sustaining Voltage	$I_C = 0.2A$ $L = 25mH$ for <b>BUV18</b> for <b>BUV19</b>	60 80			V V
$V_{EBO}$	Emitter-base Voltage ( $I_C = 0$ )	$I_E = 50mA$	7			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 40A$ $I_B = 4A$ for <b>BUV18</b> $I_C = 80A$ $I_B = 8A$ for <b>BUV18</b> $I_C = 30A$ $I_B = 3A$ for <b>BUV19</b> $I_C = 60A$ $I_B = 6A$ for <b>BUV19</b>			0.6 1.5 0.6 1.2	V V V V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 80A$ $I_B = 8A$ for <b>BUV18</b> $I_C = 60A$ $I_B = 6A$ for <b>BUV19</b>			2.2 2	V V
$f_T$	Transition Frequency	$f = 10MHz$ $V_{CE} = 15A$ $I_C = 2A$	8			MHz

**RESISTIVE LOAD**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{on}$ $t_s$ $t_f$	Turn-on Time Storage Time Fall Time	for <b>BUV18</b> $V_{CC} = 60V$ $I_C = 80A$ $I_{B1} = -I_{B2} = 8A$		1.2 0.6 0.18	1.5 1.1 0.25	$\mu s$ $\mu s$ $\mu s$
$t_s$ $t_f$	Storage Time Fall Time	for <b>BUV18</b> $V_{CC} = 60V$ $I_C = 80A$ $I_{B1} = -I_{B2} = 8A$ $T_c = 125^{\circ}C$			1.7 0.5	$\mu s$ $\mu s$
$t_{on}$ $t_s$ $t_f$	Turn-on Time Storage Time Fall Time	for <b>BUV19</b> $V_{CC} = 80V$ $I_C = 60A$ $I_{B1} = -I_{B2} = 6A$		0.9 0.6 0.17	1.3 1.1 0.25	$\mu s$ $\mu s$ $\mu s$
$t_s$ $t_f$	Storage Time Fall Time	for <b>BUV19</b> $V_{CC} = 80V$ $I_C = 60A$ $I_{B1} = -I_{B2} = 6A$ $T_c = 125^{\circ}C$			1.7 0.5	$\mu s$ $\mu s$

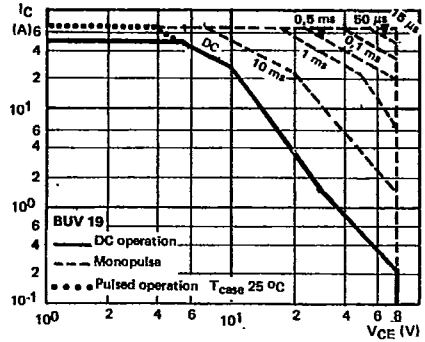
\* Pulsed : Pulse duration = 300 $\mu s$ , duty cycle = 2%

DC and AC Pulse Area.

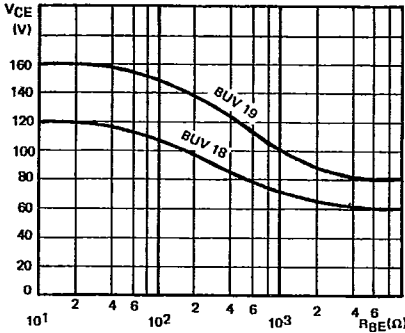


DC and AC Pulse Area.

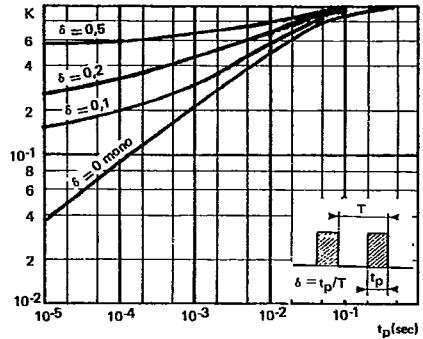
T-33-15



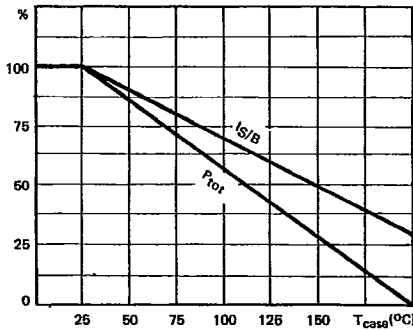
Collector-emitter Voltage vs. Base-emitter Resistance.



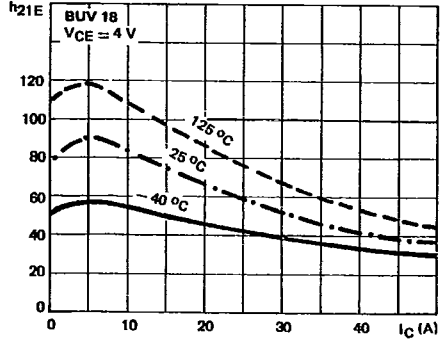
Transient Thermal Response.



Power and  $I_{S/B}$  Derating vs. Case Temperature.



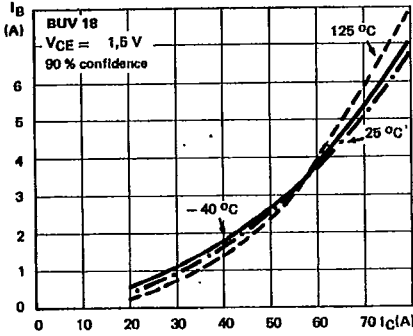
DC Current Gain.



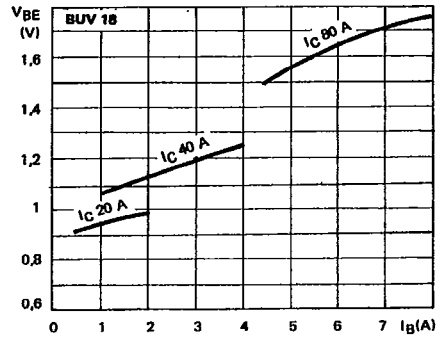
SGS-THOMSON

30E D

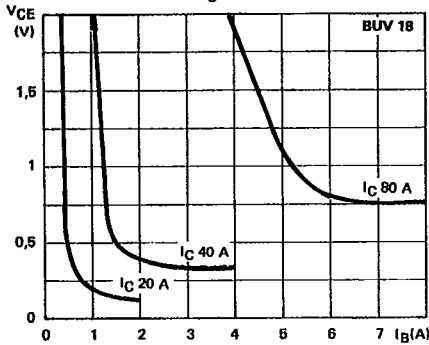
Minimum Base Current to Saturate the Transistor.



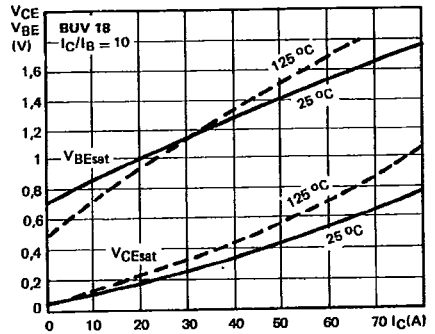
Base Characteristics.



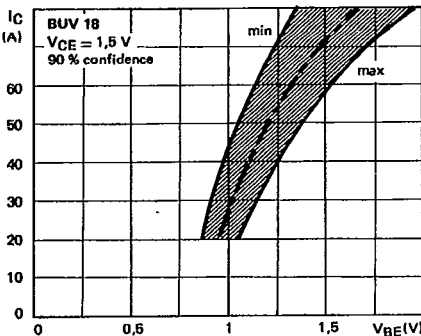
Collector Saturation Region.



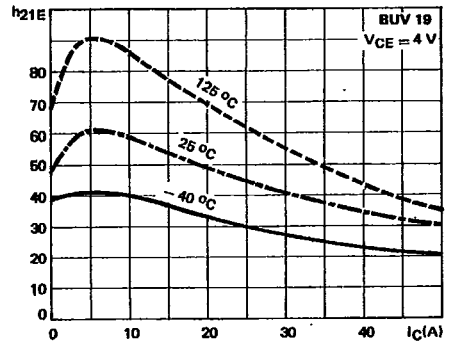
Saturation Voltage.



Collector Current Spread vs Base Emitter Voltage.



DC Current Gain.

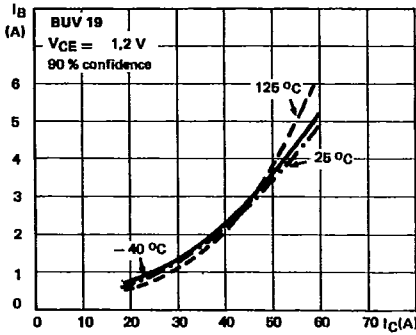


SGS-THOMSON

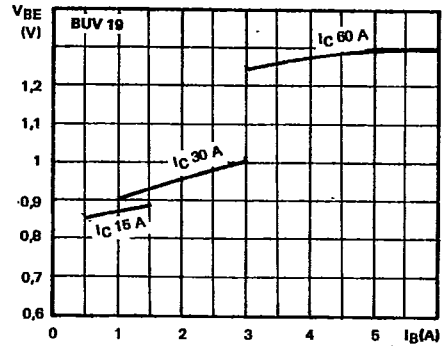
30E D

T-33-15

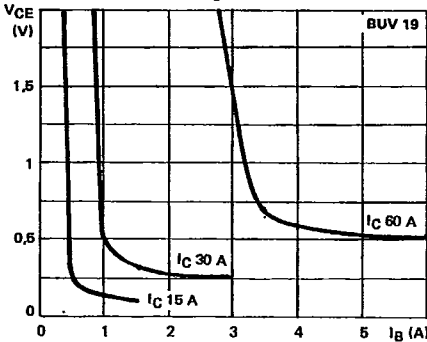
Minimum Base Current to Saturate the Transistor.



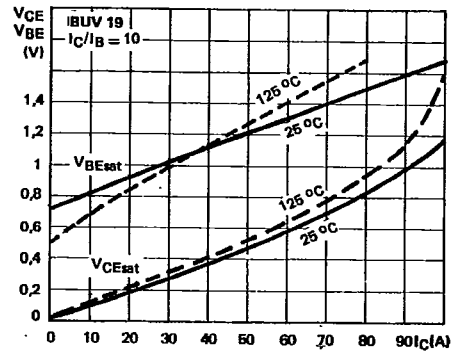
Base Characteristics.



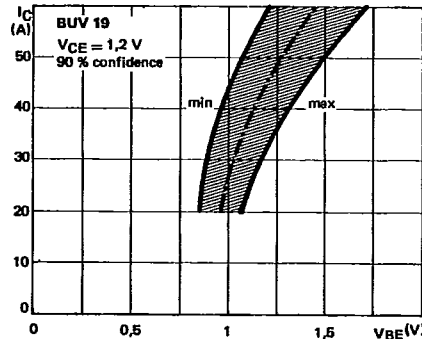
Collector Saturation Region.



Saturation Voltage.



Collector Current Spread vs Base Emitter Voltage.



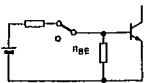
SGS-THOMSON

30E D

SWITCHING OPERATING AND OVERLOAD AREAS

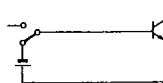
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3DE D



Transistor Forward Biased

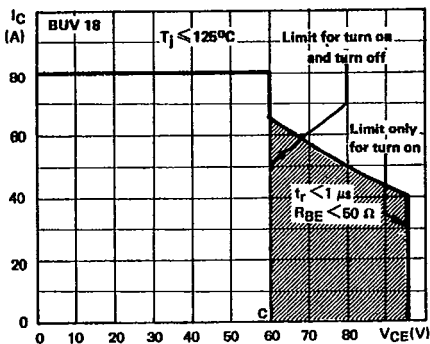
- During the turn on
- During the turn off without negative base-emitter voltage and  $R_{BE} \geq 3 \Omega$



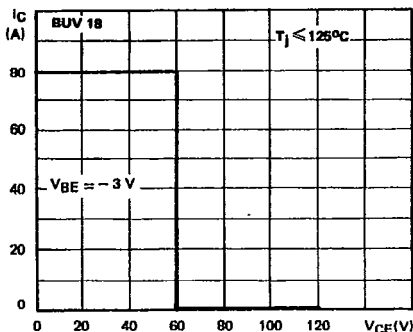
Transistor Reverse Biased

- During the turn off with negative base emitter voltage

Forward Biased Safe Operating Area (FBSOAR).

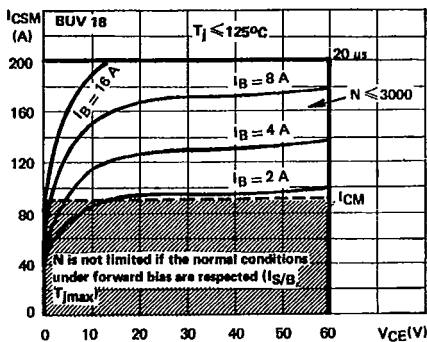


Reverse Biased Safe Operating Area (RBSOAR).

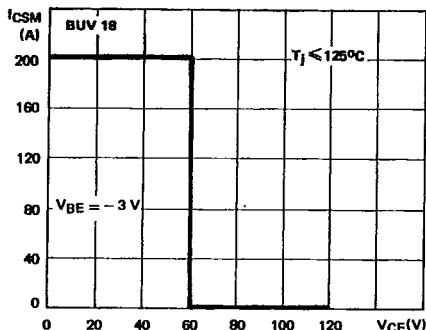


The hatched zone can only be used for turn on.

Forward Biased Accidental Overload Area (FBAOA).



Reverse Biased Accidental Overload Area (RBAOA).



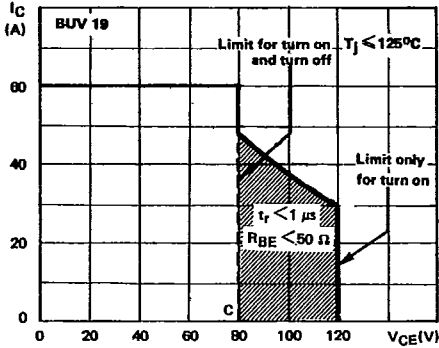
The Kellogg network (heavy print) allows the calculation of the maximum value of the short-circuit current for a given base current  $I_B$  (90 % confidence).

After the accidental overload current, the RBAOA has to be used for the turn off.

High accidental surge currents ( $I > I_{CM}$ ) are allowed if they are non repetitive and applied less than 3000 times during the component life.

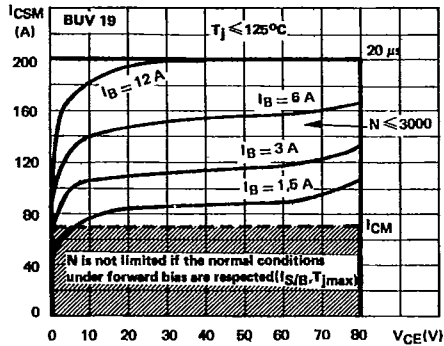
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Forward Biased Safe Operating Area (FBSOAR).



The hatched zone can only be used for turn on.

Forward Biased Accidental Overload Area (FBAOA).

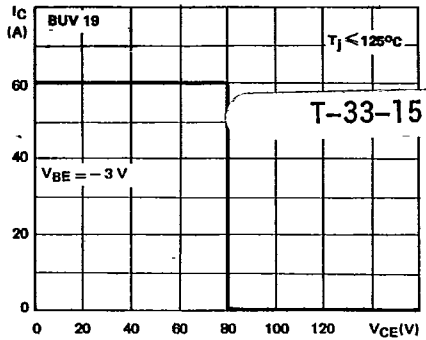


The Kellog network (heavy print) allows the calculation of the maximum value of the short-circuit current for a given base current  $I_B$  (90 % confidence).

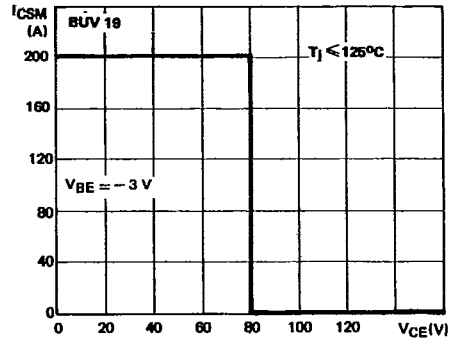
High accidental surge currents ( $I > I_{CM}$ ) are allowed if they are non repetitive and applied less than 3000 times during the component life.

3OE D

Reverse Biased Safe Operating Area (RBSOAR).



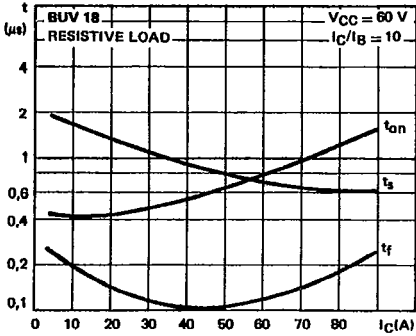
Reverse Biased Accidental Overload



After the accidental overload current, the RBAOA has to be used for the turn off.

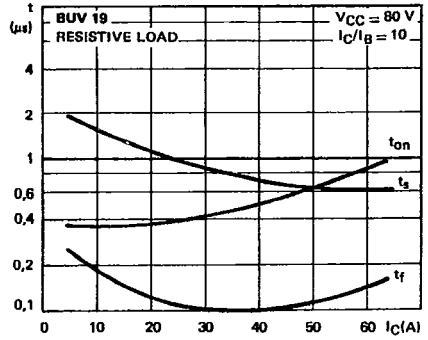
SGS-THOMSON

Switching Times vs Collector Current (resistive load).

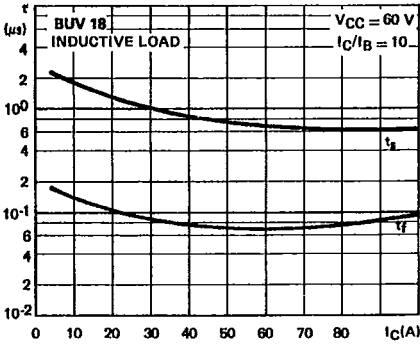


30E D

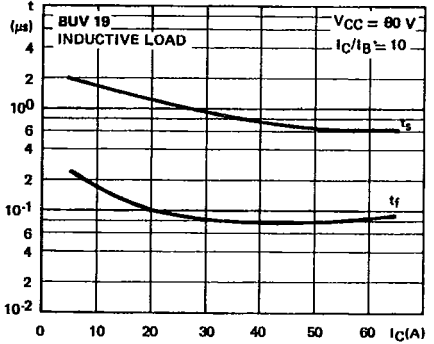
Switching Times vs Collector Current (resistive load).



Switching Times vs Collector Current.



Switching Times vs Collector Current.



Switching Times vs Junction Temperature.

